

2Mb (128K x 16) Pseudo Static RAM

Features

- Wide voltage range: **2.70V–3.30V**
- Access Time: 70ns
- Ultra-low active power
 - **Typical active current: 2.0mA @ f = 1 MHz**
 - **Typical active current: 13mA @ f = f_{max}**
- Ultra low standby power
- Automatic power-down when deselected
- CMOS for optimum speed/power
- Offered in a 48 Ball BGA Package

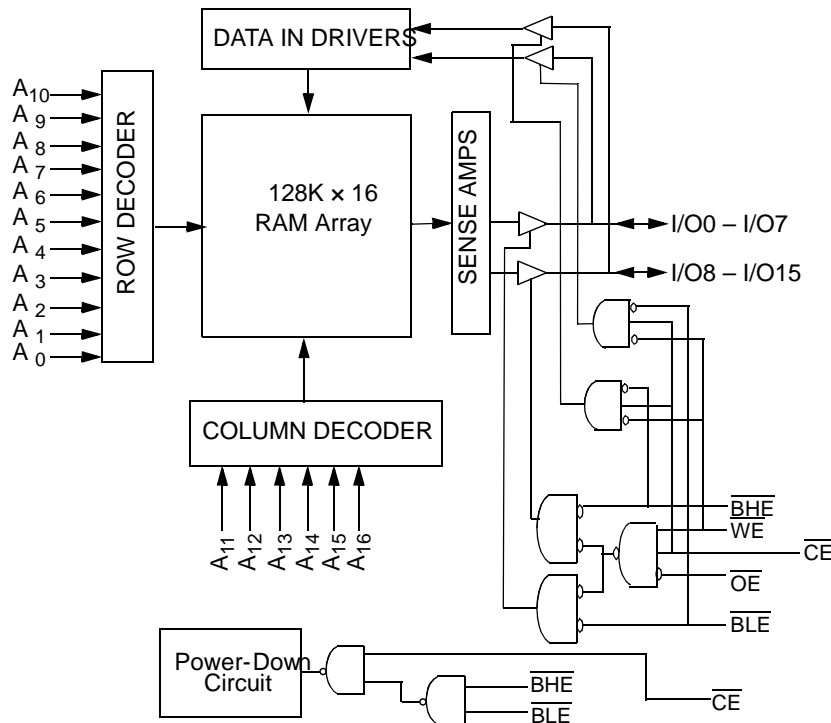
Functional Description^[1]

The CG6263AM is a high-performance CMOS Pseudo static RAM organized as 128K words by 16 bits that supports an asynchronous memory interface. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life® (MoBL) in portable applications such as cellular telephones. The device can be put into standby mode reducing power consumption by more than 99% The device can also be put into standby mode

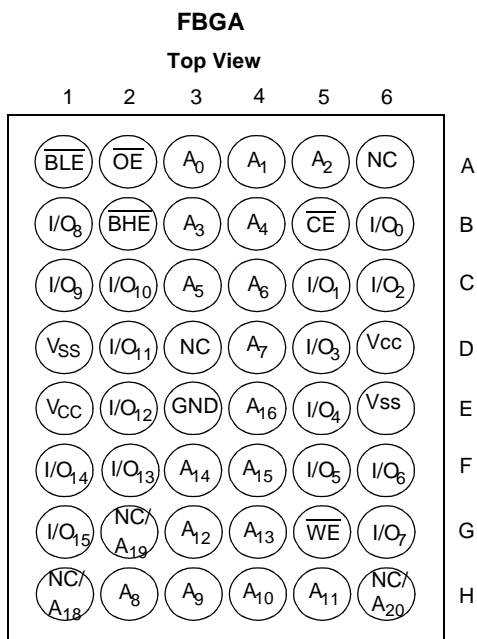
when deselected ($\overline{\text{CE}}$ HIGH or both $\overline{\text{BHE}}$ and $\overline{\text{BLE}}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{\text{CE}}$ HIGH), outputs are disabled ($\overline{\text{OE}}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{\text{BHE}}$, $\overline{\text{BLE}}$ HIGH), or during a write operation ($\overline{\text{CE}}$ LOW and $\overline{\text{WE}}$ LOW). **The addresses must not be toggled once the read is started on the device.**

Writing to the device is accomplished by taking Chip Enables (CE LOW) and Write Enable (WE) input LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O₀ through I/O₇), is written into the location specified on the address pins (A₀ through A₁₇). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₁₇).

Logic Block Diagram



Pin Configuration^[2, 3, 4]



Note:

2. DNU pins have to be left floating.
3. Ball D3, H1, G2 and ball H6 for the FBGA package can be used to upgrade to a 4M, 8M, 16M and a 32M density respectively.
4. NC "no connect" - not connected internally to the die.



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to + 150°C

Ambient Temperature with

Power Applied -55°C to + 125°C

Supply Voltage to Ground Potential -0.4V to 4.6V

DC Voltage Applied to Outputs

in High Z State^[5, 6, 7] -0.4V to 3.3V

DC Input Voltage^[5, 6, 7] -0.4V to 3.3V

Output Current into Outputs (LOW) 20 mA

Static Discharge Voltage >2001V
(per MIL-STD-883, Method 3015)

Latch-Up Current >200 mA

Operating Range^[9]

Device	Range	Ambient Temperature	V _{CC}
CG6263AM	Industrial	-25°C to +85°C	2.70V to 3.30V

Product Portfolio

Product	V _{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I _{CC} (mA)				Standby I _{SB2} (μA)	
					f = 1MHz		f = f _{max}			
	Min.	Typ. ^[8]	Max.		Typ. ^[8]	Max.	Typ. ^[8]	Max.	Typ. ^[8]	Max.
CG6263AM	2.70	3.0	3.30	70	2	4	13	17	55	80

Notes:

5. V_{IL(MIN)} = -0.5V for pulse durations less than 20ns.
6. V_{IH(Max)} = V_{CC} + 0.5V for pulse durations less than 20ns.
7. Overshoot and undershoot specifications are characterized and are not 100% tested.
8. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ.)}, T_A = 25°C.
9. V_{CC} must be at minimal operational levels before inputs are turned ON.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	CG6263AM-70			Unit
			Min.	Typ. ^[8]	Max.	
V _{CC}	Supply Voltage		2.7		3.3	V
V _{OH}	Output HIGH Voltage	I _{OH} = -1.0 mA, V _{CC} = 2.70V	2.4			V
V _{OL}	Output LOW Voltage	I _{OL} = 2.0mA, V _{CC} = 2.70V			0.4	V
V _{IH}	Input HIGH Voltage	V _{CC} = 2.7V to 3.3V	0.8*V _{CC}		V _{CC} + 0.3V	V
V _{IL}	Input LOW Voltage	V _{CC} = 2.7V to 3.3V (F = 0)	-0.3		0.4	V
I _{IX}	Input Leakage Current	GND ≤ V _I ≤ V _{CC}	-1		+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled	-1		+1	μA
I _{CC}	V _{CC} Operating Supply Current	f = f _{MAX} = 1/t _{RC}		13	17	mA
		f = 1 MHz, V _{CC} = V _{CCmax} , I _{OUT} = 0 mA, CMOS levels		2.0	4	mA
I _{SB1}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V, V_{IN} \leq 0.2V$ f = f _{MAX} (Address and Data Only), f = 0 (\overline{OE} , \overline{WE} , \overline{BHE} and \overline{BLE}), V _{CC} = 3.30V			350	μA
I _{SB2}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, f = 0, V _{CC} = 3.30V		55	80	μA

Capacitance^[10]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = V _{CC(typ)}	6	pF
C _{OUT}	Output Capacitance		8	pF

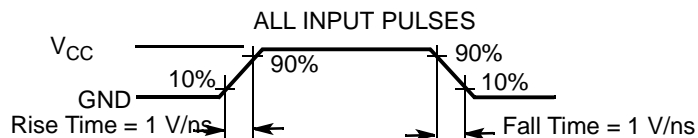
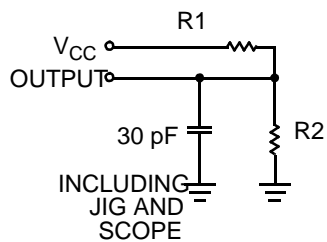
Thermal Resistance^[10]

Description	Test Conditions	Symbol	BGA	Unit
Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	Θ _{JA}	55	°C/W
Thermal Resistance (Junction to Case)		Θ _{JC}	16	°C/W

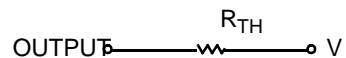
Note:

10. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Equivalent to: THÉVENINEQUIVALENT



Parameters	3.0V V _{CC}	Unit
R ₁	1179	Ω
R ₂	1941	Ω
R _{TH}	733	Ω
V _{TH}	1.87	V

Switching Characteristics Over the Operating Range^[11]

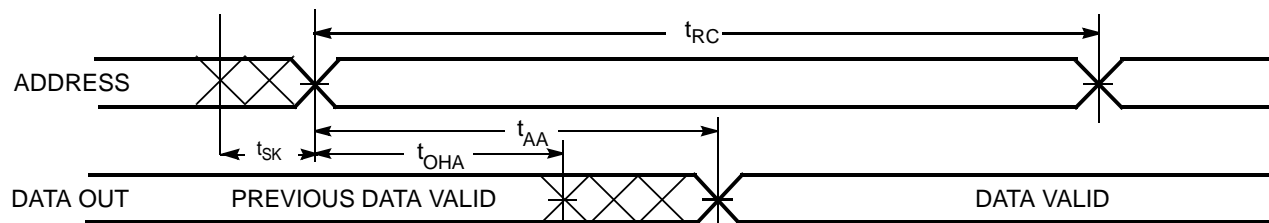
Parameter	Description	70 ns		Unit
		Min.	Max.	
READ CYCLE				
t _{RC}	Read Cycle Time	70		ns
t _{AA}	Address to Data Valid		70	ns
t _{OHA}	Data Hold from Address Change	10		ns
t _{ACE}	\overline{CE} LOW to Data Valid		70	ns
t _{DOE}	\overline{OE} LOW to Data Valid		35	ns
t _{LZOE}	\overline{OE} LOW to LOW Z ^[12, 14]	5		ns
t _{HZOE}	\overline{OE} HIGH to High Z ^[12, 14]		25	ns
t _{LZCE}	\overline{CE} LOW to Low Z ^[12, 14]	5		ns
t _{HZCE}	\overline{CE} HIGH to High Z ^[12, 14]		25	ns
t _{DBE}	BLE / BHE LOW to Data Valid		70	ns
t _{LZBE}	\overline{BLE} / \overline{BHE} LOW to Low Z ^[12, 14]	5		ns
t _{HZBE}	\overline{BLE} / \overline{BHE} HIGH to HIGH Z ^[12, 14]		25	ns
t _{sk}	Address Skew		0	ns
WRITE CYCLE ^[13]				
t _{WC}	Write Cycle Time	70		ns
t _{SCE}	\overline{CE} LOW to Write End	60		ns
t _{AW}	Address Set-Up to Write End	60		ns
t _{HA}	Address Hold from Write End	0		ns
t _{SA}	Address Set-Up to Write Start	0		ns
t _{PWE}	\overline{WE} Pulse Width	45		ns
t _{BW}	\overline{BLE} / \overline{BHE} LOW to Write End	60		ns
t _{SD}	Data Set-Up to Write End	45		ns
t _{HD}	Data Hold from Write End	0		ns
t _{HZWE}	\overline{WE} LOW to High-Z ^[12, 14]		25	ns
t _{LZWE}	\overline{WE} HIGH to Low-Z ^[12, 14]	5		ns

Notes:

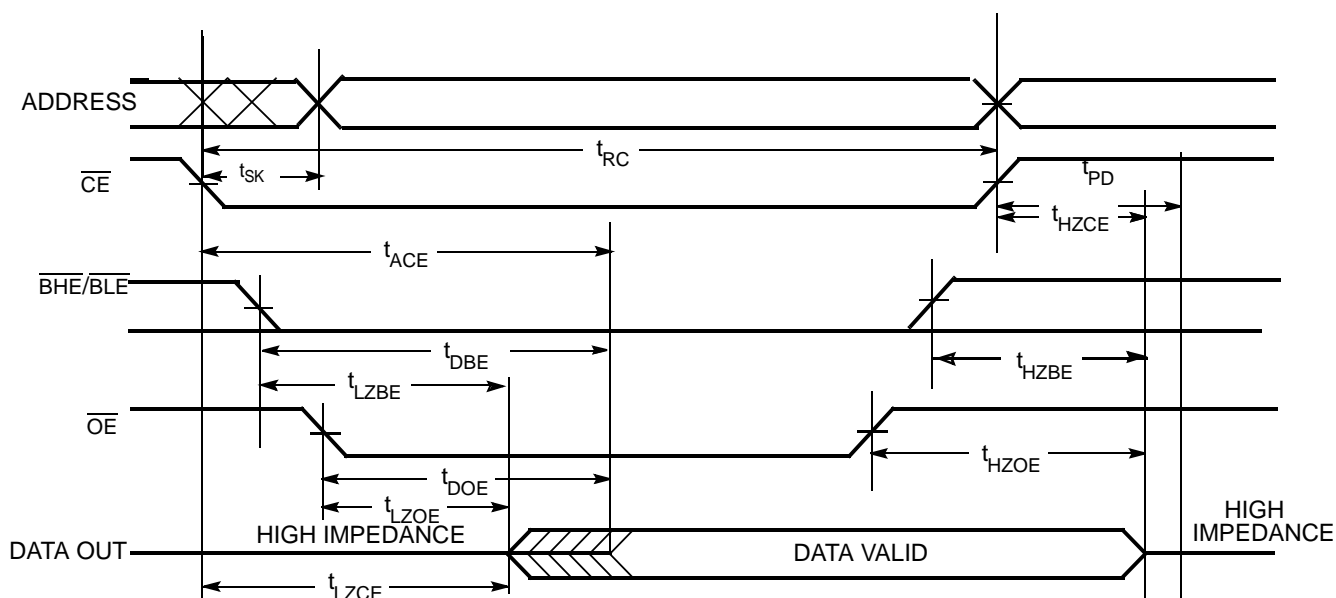
11. Test conditions for all parameters other than tri-state parameters assume signal transition time of 1ns/V, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0V to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" section..
12. t_{HZOE} , t_{HZCE} , t_{HZBE} , and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
13. The internal Write time of the memory is defined by the overlap of \overline{WE} , $\overline{CE} = V_{IL}$, \overline{BHE} and/or $\overline{BLE} = V_{IL}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write
14. High-Z and Low-Z parameters are characterized and are not 100% tested. .

Switching Waveforms

Read Cycle 1 (Address Transition Controlled)^[15, 16]



Read Cycle 2 ($\overline{\text{OE}}$ Controlled)^[15, 16]

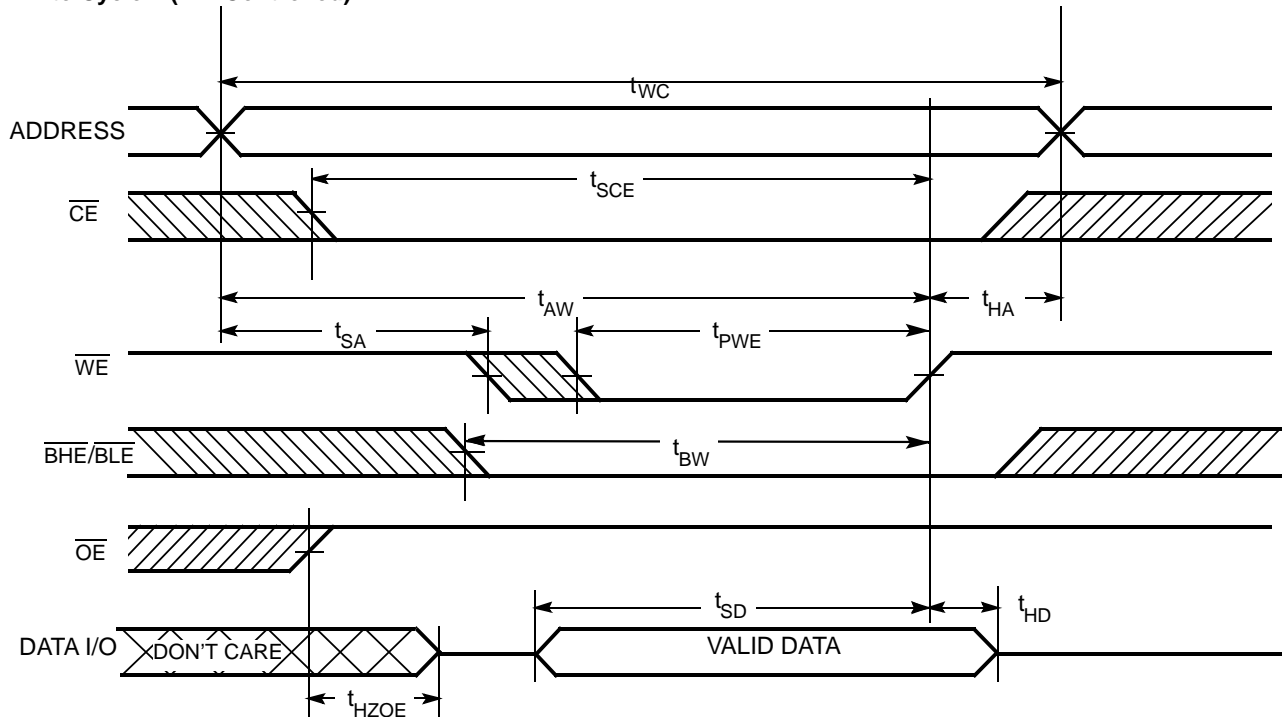


Note:

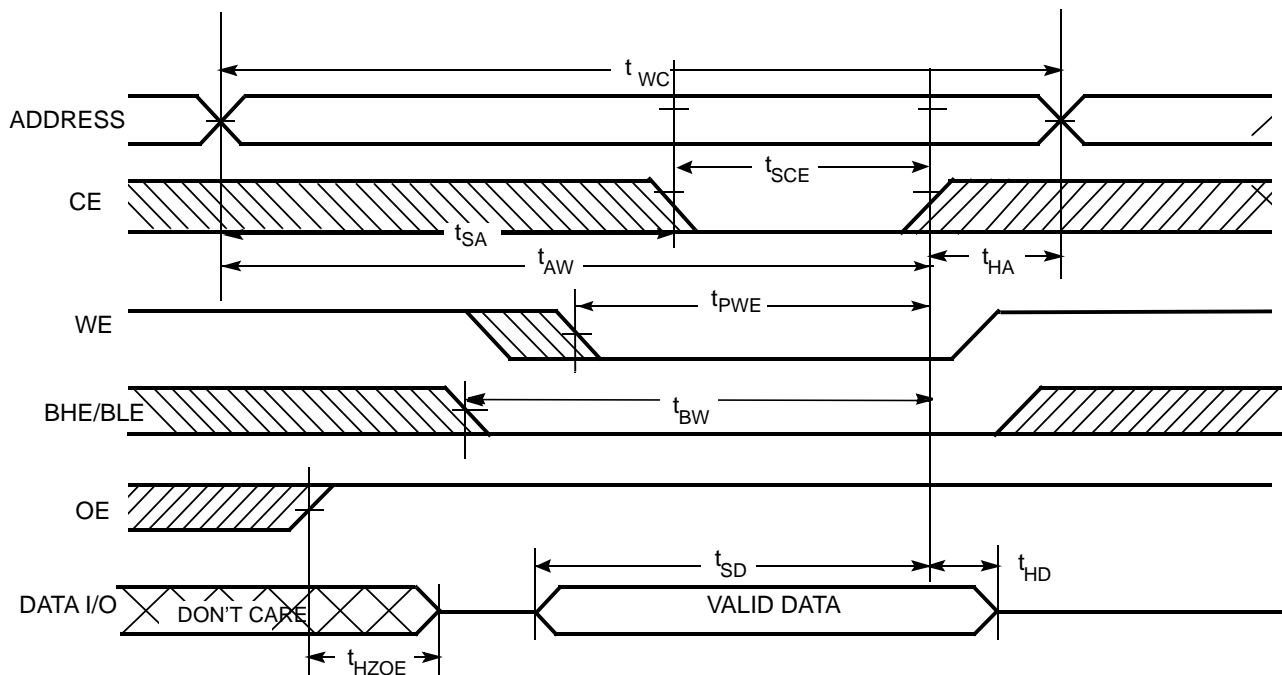
15. $\overline{\text{WE}}$ is HIGH for Read Cycle.
16. Addresses should not be toggled after the start of a read cycle

Switching Waveforms (continued)

Write Cycle 1 (\overline{WE} Controlled) [13, 14, 17, 18, 19]



Write Cycle 2 (\overline{CE} Controlled) [13, 14, 17, 18, 19]

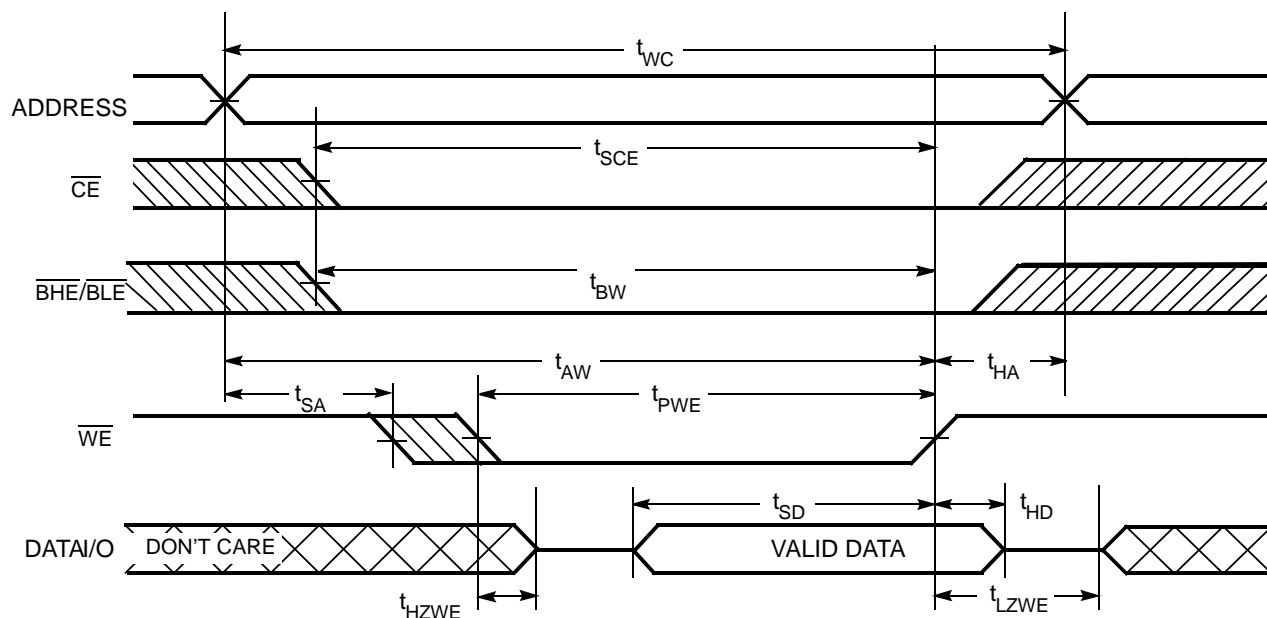


Notes:

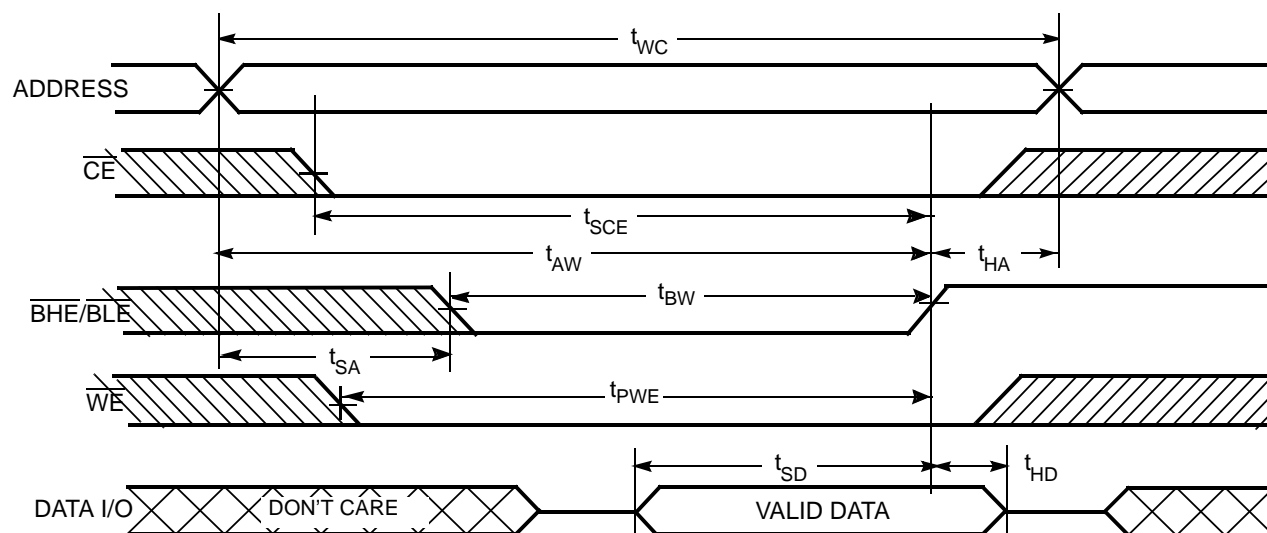
17. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
18. If Chip Enable goes INACTIVE with $WE = V_{IH}$, the output remains in a high-impedance state.
19. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[18, 19]



Write Cycle 4 ($\overline{\text{BHE/BLER}}$ Controlled, $\overline{\text{OE}}$ LOW)^[18, 19]



Truth Table^[20]

CE	WE	OE	BHE	BLE	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
X	X	X	H	H	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O0 – I/O15)	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O0 – I/O7); High Z (I/O8 – I/O15)	Read	Active (I_{CC})
L	H	L	L	H	High Z (I/O0 – I/O7); Data Out (I/O8 – I/O15)	Read	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O0 – I/O15)	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O0 – I/O7); High Z (I/O8 – I/O15)	Write	Active (I_{CC})
L	L	X	L	H	High Z (I/O0 – I/O7); Data In (I/O8 – I/O15)	Write	Active (I_{CC})

Note:

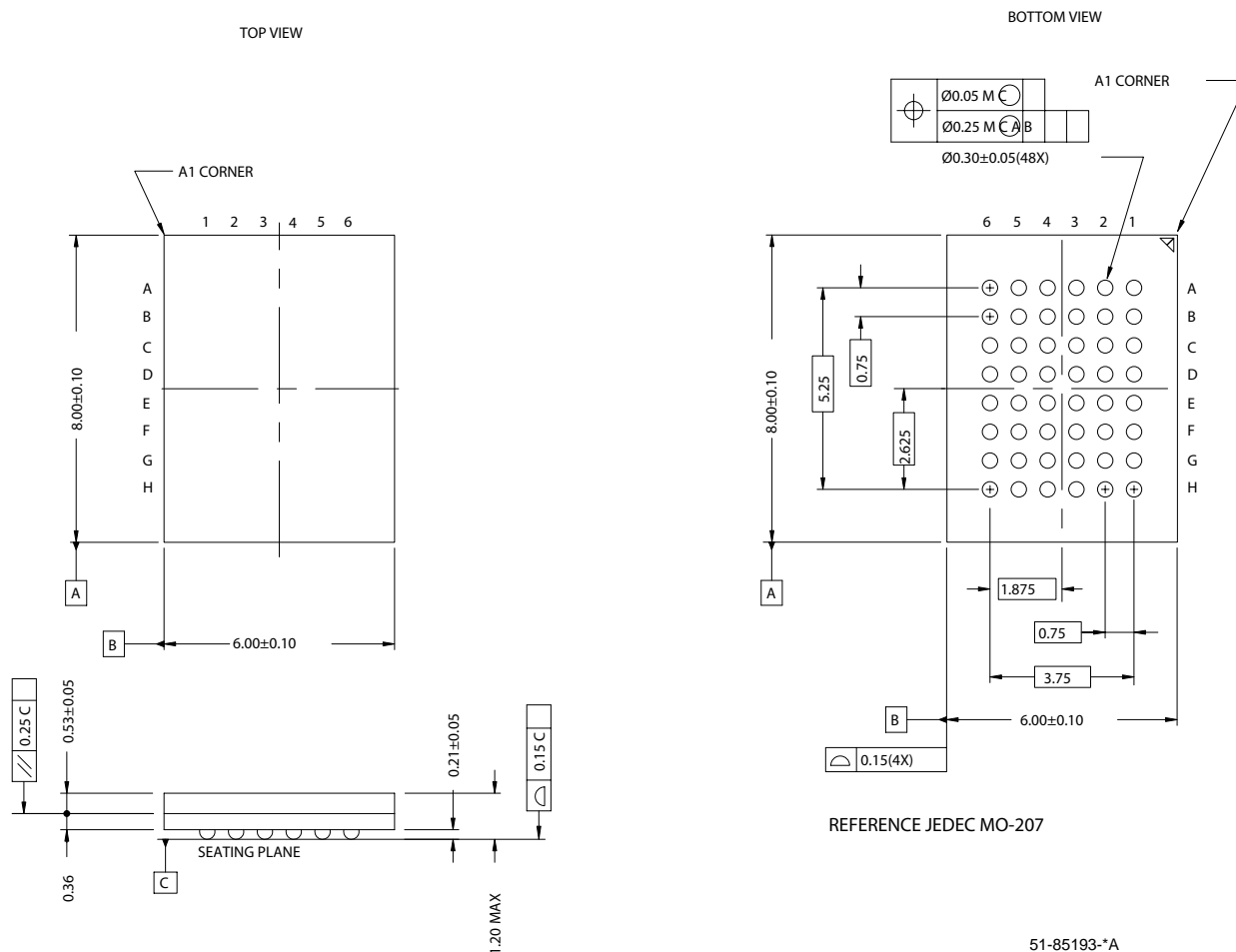
20. H = V_{IH} , L = V_{IL} , X = Don't Care

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CG6263AM	BA48K	48-ball Fine Pitch BGA (6 mm × 8mm × 1.2 mm)	Industrial

Package

48-Ball (6 mm x 8mm x 1.2 mm) FBGA BA48K



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PRELIMINARY

CG6263AM

Document Title: CG6263AM MoBL3 [®] 2Mb (128K x 16) Pseudo Static RAM Document Number: 38-XXXXX				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**		10/21/03	MPR	New Datasheet